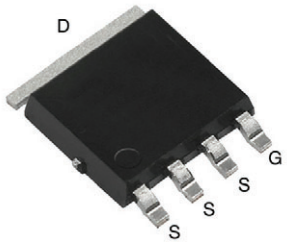
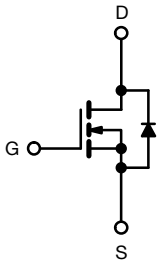
E Series Power MOSFET

PowerPAK® SO-8L





N-Channel MOSFET

FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) R_{on} x Q_g
- Low effective capacitance ($C_{o(er)}$)
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Switch mode power supplies (SMPS)
- Flyback converter
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Consumer
  - Wall adaptors

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ typ. (Ω) at 25 °C	V_{GS} = 10 V	0.60
Q_g max. (nC)	12	
Q_{gs} (nC)	3	
Q_{gd} (nC)	3	
Configuration	Single	

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SiHJ690N60E-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	600	V
Gate-source voltage			V_{GS}	± 30	
Continuous drain current (T_J = 150 °C)	V_{GS} at 10 V	T_C = 25 °C	I_D	5.6	A
		T_C = 100 °C		3.5	
Pulsed drain current [a]			I_{DM}	11	
Linear derating factor				0.38	W/°C
Single pulse avalanche energy [b]			E_{AS}	9	mJ
Maximum power dissipation			P_D	48	W
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope		T_J = 125 °C	dv/dt	70	V/ns
Reverse diode dv/dt [d]				17	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature
b. V_{DD} = 120 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 0.8 A
c. 1.6 mm from case

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	52	65	°C/W
Maximum junction-to-case (drain)	R_{thJC}	1.9	2.6	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	600	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	0.73	-	V/°C
Gate-source threshold voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	3.0	-	5.0	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
		V_{GS} = ± 30 V	-	-	± 1	µA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V	-	-	1	µA
		V_{DS} = 480 V, V_{GS} = 0 V, T_J = 125 °C	-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 2.0 A	-	0.60	0.70	Ω
Forward transconductance [a]	g_{fs}	V_{DS} = 20 V, I_D = 2.0 A	-	1.2	-	S
Dynamic						
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz	-	347	-	pF
Output capacitance	C_{oss}		-	24	-	
Reverse transfer capacitance	C_{rss}		-	4	-	
Effective output capacitance, energy related [a]	$C_{o(er)}$	V_{DS} = 0 V to 480 V, V_{GS} = 0 V	-	17	-	
Effective output capacitance, time related [b]	$C_{o(tr)}$		-	86	-	
Total gate charge	Q_g	V_{GS} = 10 V; I_D = 2.0 A, V_{DS} = 480 V	-	8	12	nC
Gate-source charge	Q_{gs}		-	3	-	
Gate-drain charge	Q_{gd}		-	3	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 480 V, I_D = 2.0 A, V_{GS} = 10 V, R_g = 9.1 Ω	-	12	24	ns
Rise time	t_r		-	9	18	
Turn-off delay time	$t_{d(off)}$		-	19	38	
Fall time	t_f		-	22	44	
Gate input resistance	R_g	f = 1 MHz, open drain	1.1	2.3	4.6	Ω
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	5.6	A
Pulsed diode forward current	I_{SM}		-	-	11	
Diode forward voltage	V_{SD}	T_J = 25 °C, I_S = 2.0 A, V_{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t_{rr}	T_J = 25 °C, I_F = I_S = 2.0 A, di/dt = 100 A/µs, V_R = 25 V	-	146	292	ns
Reverse recovery charge	Q_{rr}		-	1.0	2.0	µC
Reverse recovery current	I_{RRM}		-	13	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

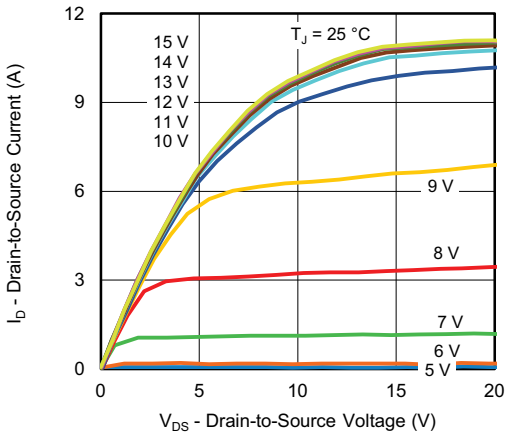


Fig. 1 - Typical Output Characteristics

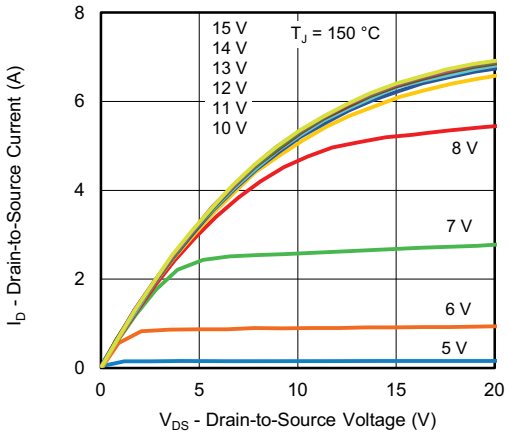


Fig. 2 - Typical Output Characteristics

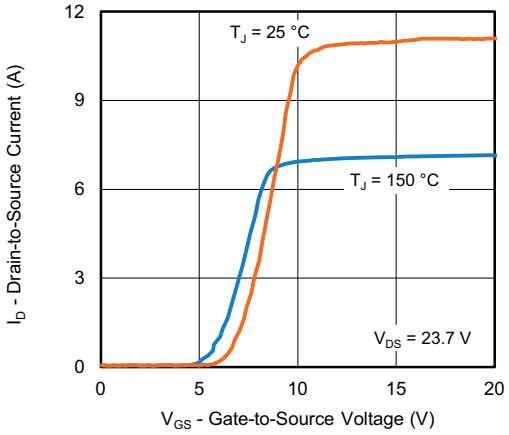


Fig. 3 - Typical Transfer Characteristics

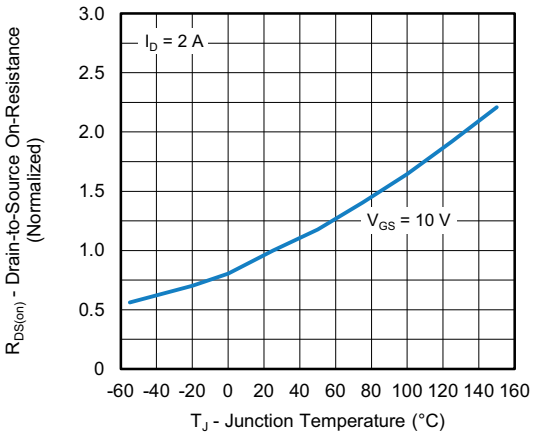


Fig. 4 - Normalized On-Resistance vs. Temperature

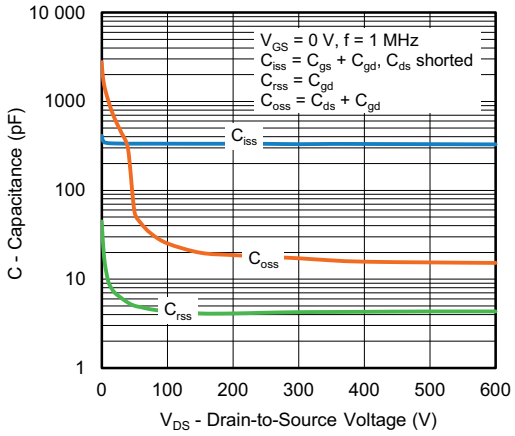


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

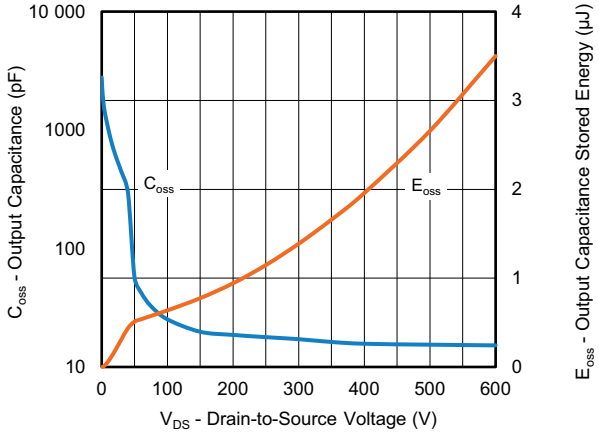


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

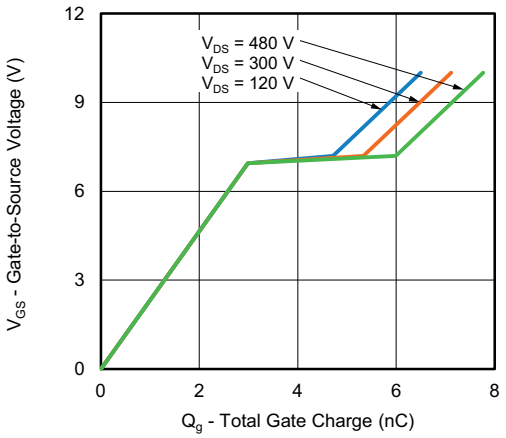


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

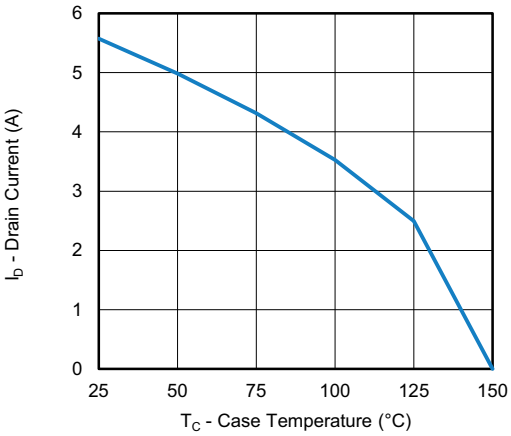


Fig. 10 - Maximum Drain Current vs. Case Temperature

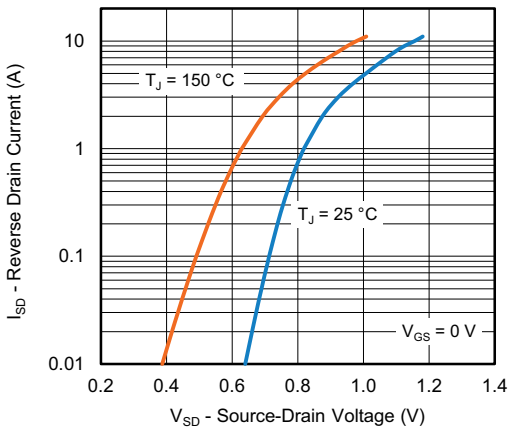


Fig. 8 - Typical Source-Drain Diode Forward Voltage

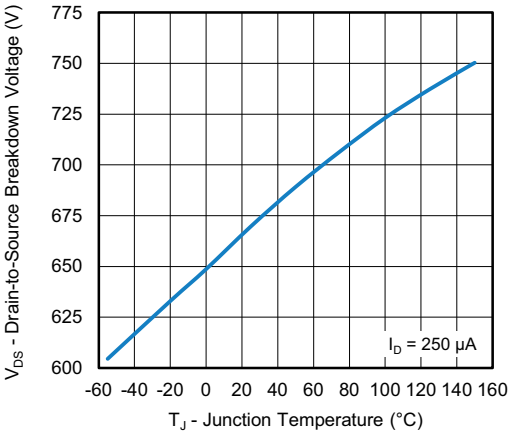


Fig. 11 - Temperature vs. Drain-to-Source Voltage

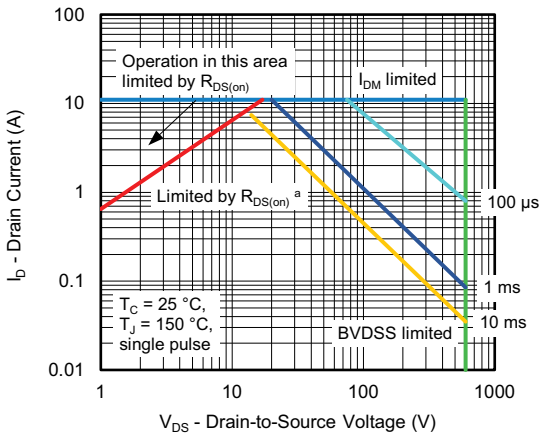


Fig. 9 - Maximum Safe Operating Area

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

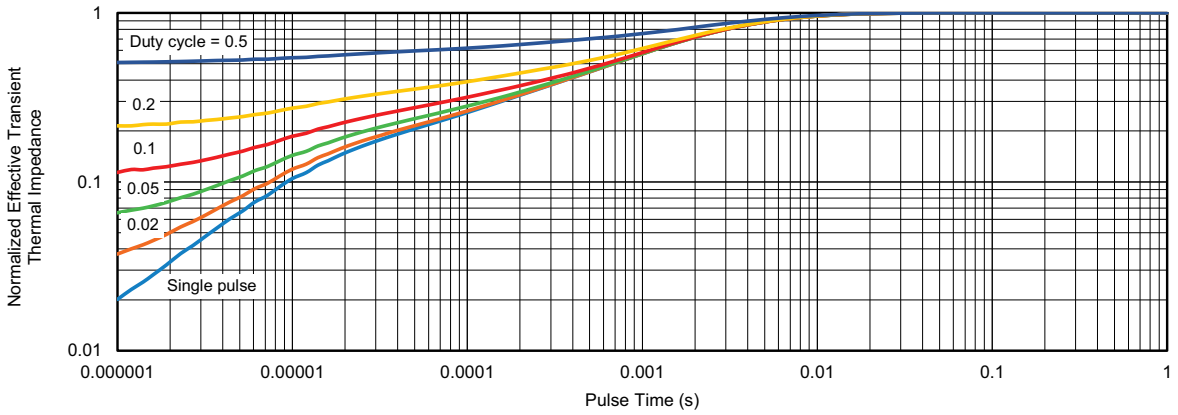


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

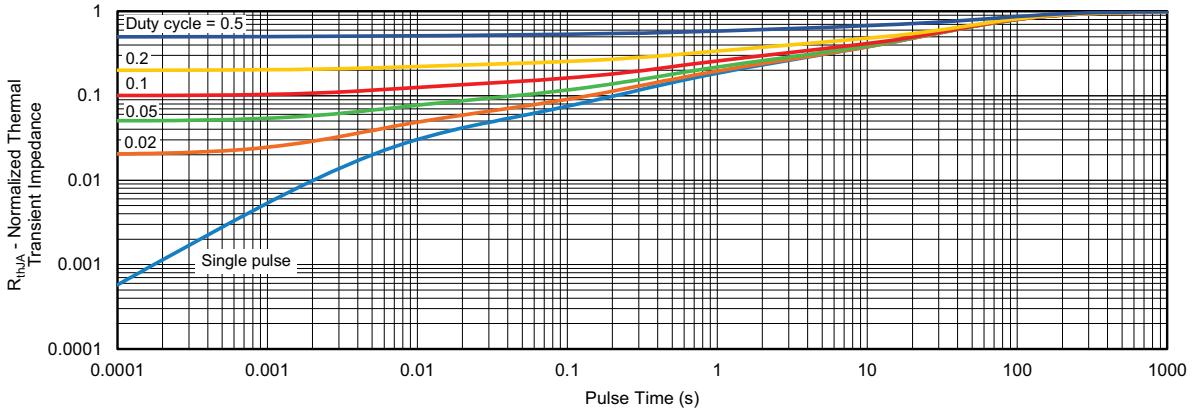


Fig. 13 - Normalized Transient Thermal Impedance, Junction-to-Ambient

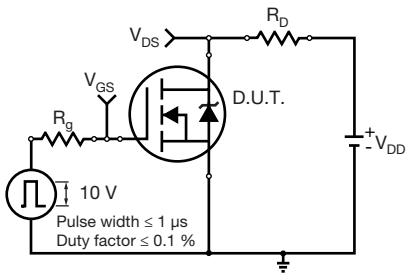


Fig. 14 - Switching Time Test Circuit

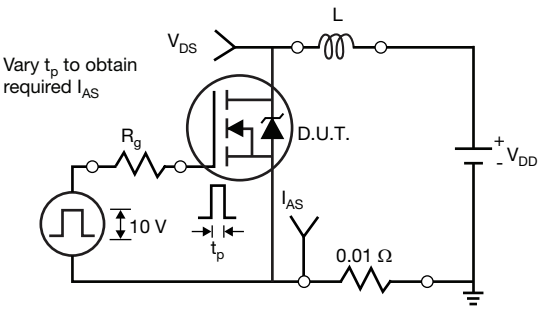


Fig. 16 - Unclamped Inductive Test Circuit

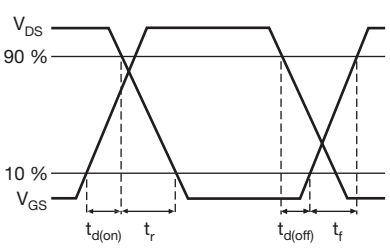


Fig. 15 - Switching Time Waveforms

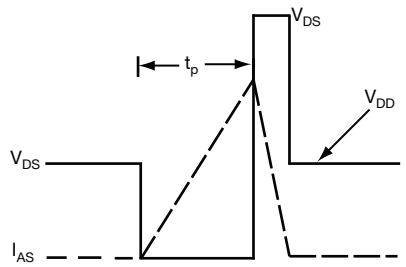


Fig. 17 - Unclamped Inductive Waveforms

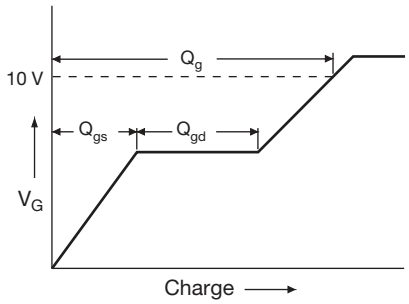


Fig. 18 - Basic Gate Charge Waveform

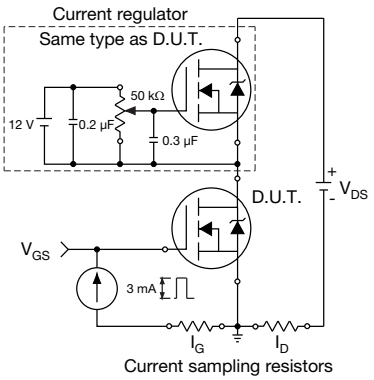
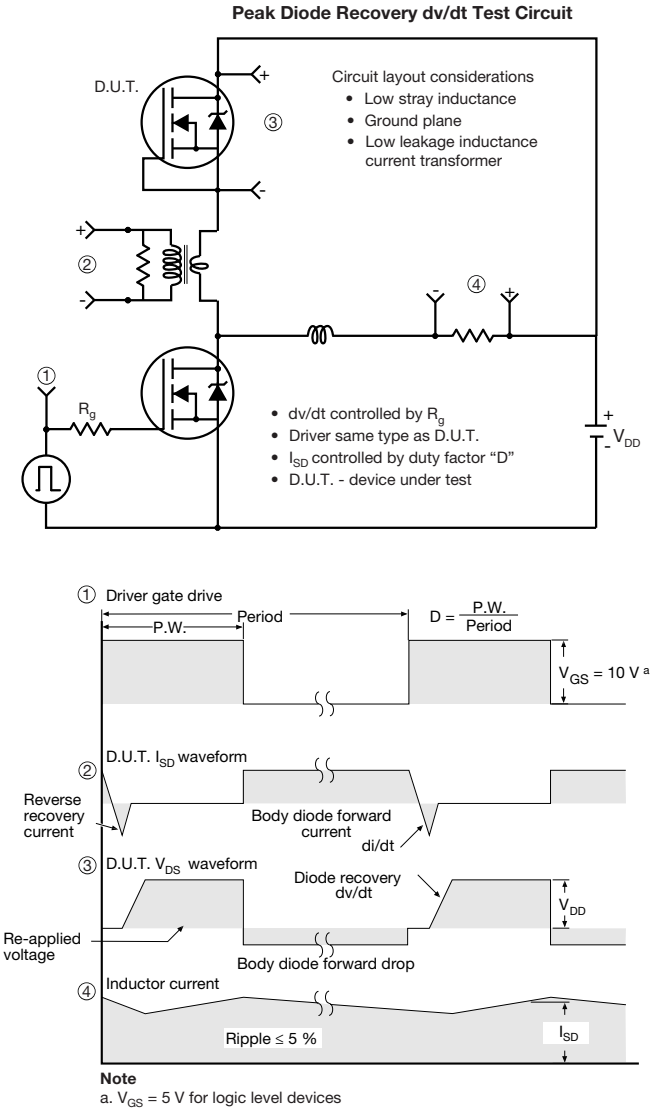


Fig. 19 - Gate Charge Test Circuit

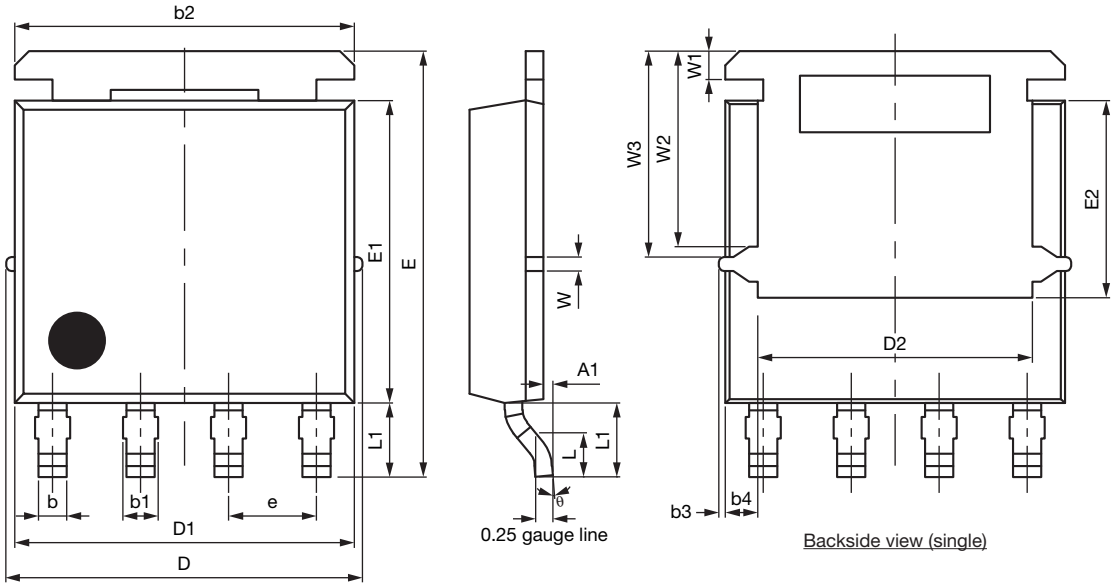


Note
a. V_{GS} = 5 V for logic level devices

Fig. 20 - For N-Channel

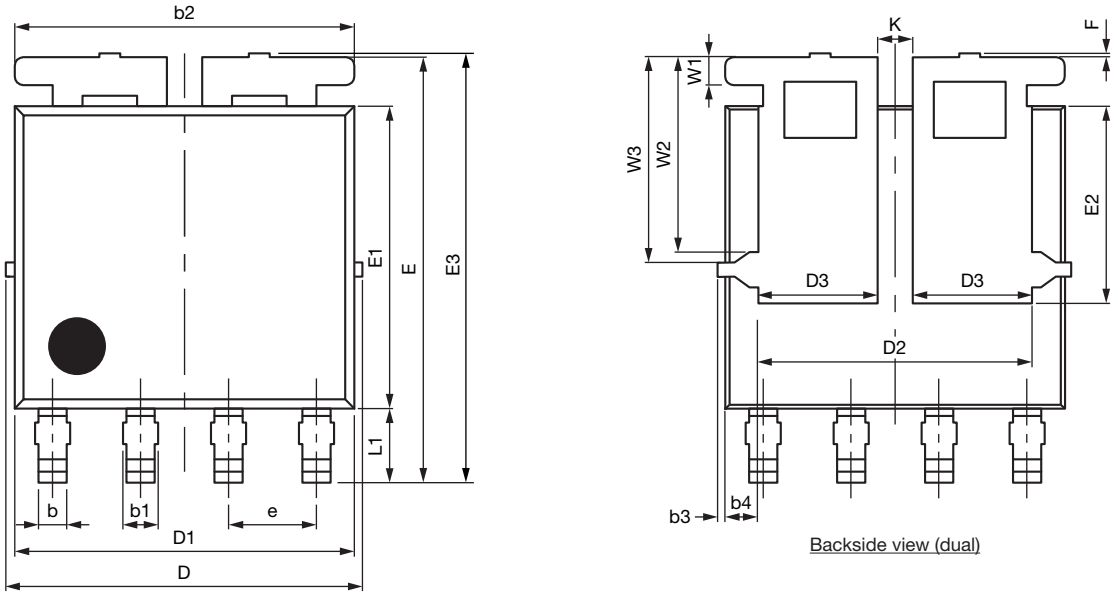
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?92276.

PowerPAK® SO-8L Case Outline 2



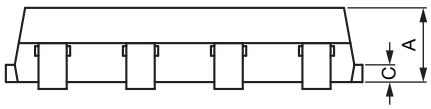
Topside view (single)

Backside view (single)



Topside view (dual)

Backside view (dual)

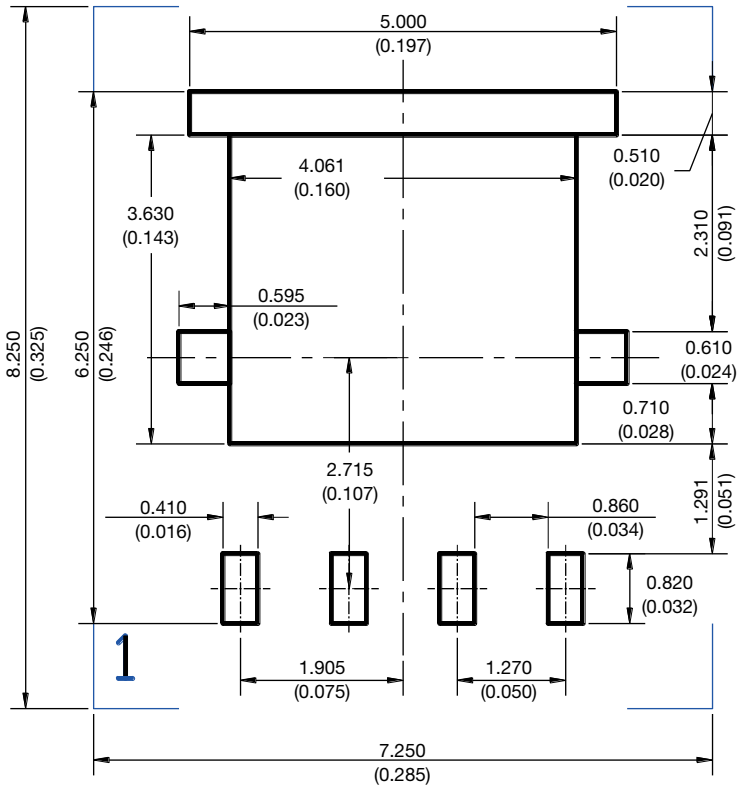


DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
E3	6.05	6.22	6.40	0.238	0.245	0.252
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°
ECN: C23-1026-Rev. D, 25-Sep-2023 DWG: 6044						

Note

- Millimeters will govern

RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads
Dimensions in mm (inches)

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